

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE01P13 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. It is ESD protested.

General Features

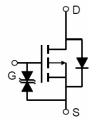
- V_{DS} =-100V, I_{D} =-13A $R_{DS(ON)}$ <200mΩ @ V_{GS} =-10V (Typ:170mΩ)
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density celldesign for ultra low on-resistance

Application

- Power switch
- DC/DC converters

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE01P13	NCE01P13	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-13	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	-9.2	А
Pulsed Drain Current	I _{DM}	-52	Α
Maximum Power Dissipation	P _D	40	W
Derating factor		0.27	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	110	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$



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Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{eJc}	3.75	°C/W	Ī
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Electrical Characteristics (Tc=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1	-1.9	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A	-	170	200	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-10A	12	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ 50\/\/ 0\/	-	1734	-	PF
Output Capacitance	C _{oss}	V _{DS} =-50V,V _{GS} =0V,	-	86	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	40	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$		-	12	-	nS
Turn-on Rise Time	t _r	V _{DD} =-50V,I _D =-10A	-	52	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =-10 V , R_{GEN} =9.1 Ω	-	28	-	nS
Turn-Off Fall Time	t _f		-	38	-	nS
Total Gate Charge	Qg	\/ F0\/ 40A	-	33.1	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-50V,I _D =-10A,	-	4.2	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =-10V	-	7.1	-	nC
Drain-Source Diode Characteristics			1			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-10A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S	-	-	-	-13	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =-10A	-	35	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	46	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negli	gible (turr	n-on is do	ominated b	y LS+LD)

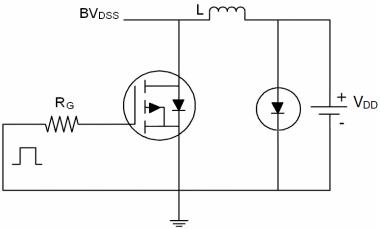
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=-50V,V_G=-10V,L=0.5mH,Rg=25 Ω

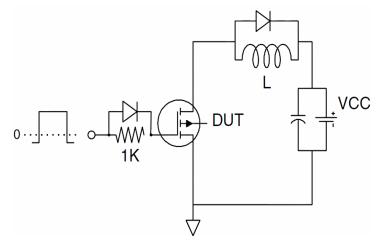


Test Circuit

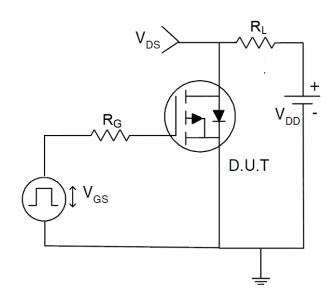
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

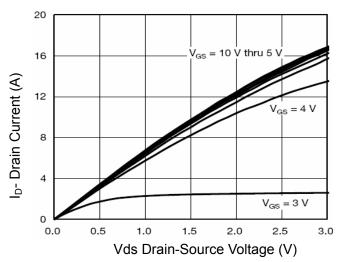


Figure 1 Output Characteristics

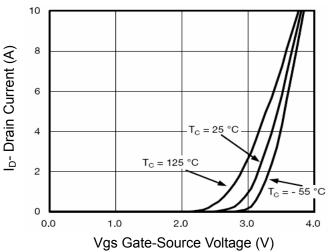


Figure 2 Transfer Characteristics

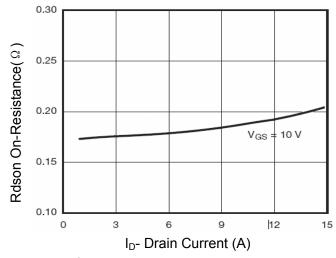


Figure 3 Rdson- Drain Current

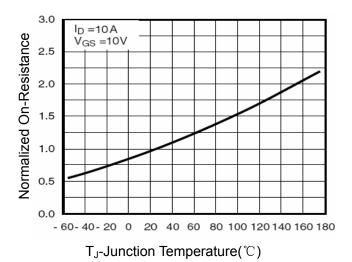


Figure 4 Rdson-JunctionTemperature

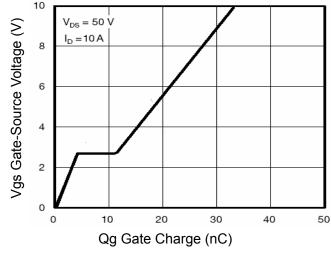


Figure 5 Gate Charge

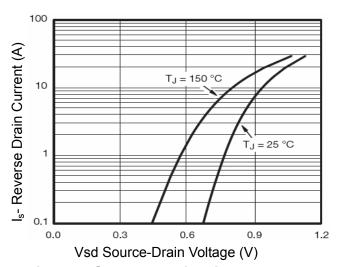


Figure 6 Source- Drain Diode Forward



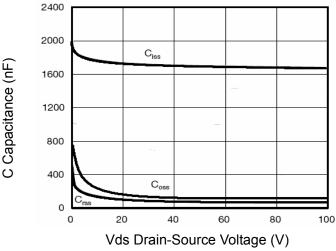


Figure 7 Capacitance vs Vds

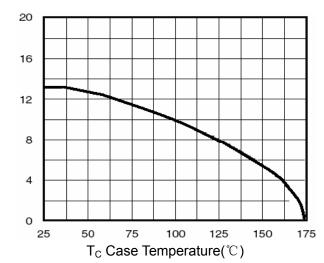


Figure 9 Drain Current vs Case Temperature

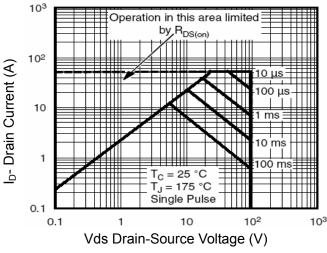


Figure 8 Safe Operation Area

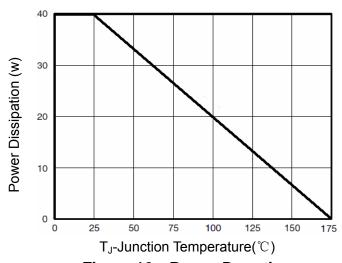
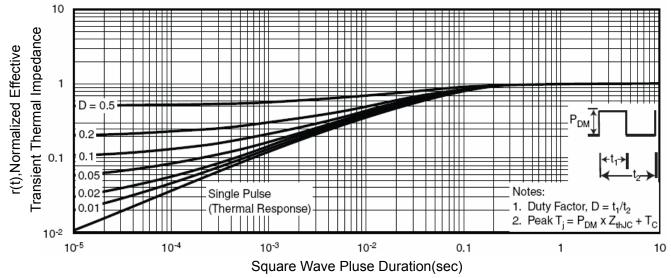


Figure 10 Power De-rating

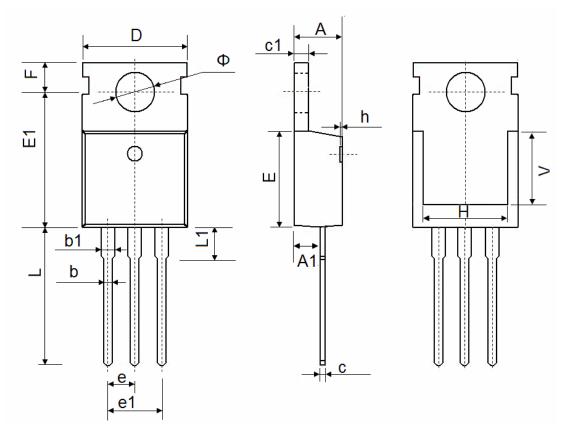


ID- Drain Current (A)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



Complete	Dimension	s In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	10 TYP.	0.100	TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.50	7.500 REF.		REF.	
Ф	3.400	3.800	0.134	0.150	



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